<u>PATENT</u>

<u>IN ŤŘE UNITED STATES PATENT AND TRADEMARK OFFICE</u>

Applicant:

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Examiner: Luong Nguyen

Serial No.:

09/136,680

Group Art Unit: 2612

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Title:

CMOS IMAGER WITH INTEGRATED NON-VOLATILE MEMORIECEIVED

## AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

DEC 1 8 2002

Technology Center 2600

Commissioner for Patents Washington, D.C. 20231

This paper is in response to the Office Action mailed on <u>September 12, 2002</u>. Please amend the above-identified patent application as follows.

## IN THE DRAWINGS

Enclosed are a copy of each of Figures 1 and 3 of the drawings showing the proposed amendments in red ink. Applicant removes the term "memory" from Figure 1. Applicant adds the substrate 110 to Figure 3. Approval of the proposed drawing amendments is requested. A new set of formal Figures 1-3 including the proposed amendments are also submitted herewith.

## **IN THE CLAIMS**

Please substitute the claim set in the appendix entitled Clean Version of Pending Claims for the previously pending claim set. The substitute claim set is intended to reflect amendment of previously pending claims 1, 4-8, 11, 15, 16, 19, 21, 22, and 25-27. The specific amendments to individual claims are detailed in the following marked up set of claims.

1. (Amended)

An image sensor [fabricated on a substrate] comprising:

a monolithic substrate;

a CMOS image sensor on the monolithic substrate and adapted for defining an image signal photoelectrically converted in response to received light;

a frame memory on the monolithic substrate and adapted for receiving the image signal from the CMOS image sensor;

an array of non-volatile memory cells on the monolithic substrate and adapted for receiving and storing the image signal from the frame memory, wherein each memory cell stores